

# **PMBD914** Single high-speed switching diode Rev. 06 — 11 February 2009

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Single high-speed switching diode, fabricated in planar technology, and encapsulated in a small Surface-Mounted Device (SMD) plastic package.

#### Table 1. **Product overview**

Type number <sup>[1]</sup>	Package		
	NXP	JEDEC	
PMBD914	SOT23	TO-236AB	
PMBD914/DG			

[1] /DG: halogen-free

### 1.2 Features

- High switching speed:  $t_{rr} \le 4$  ns
- Low leakage current
- Repetitive peak reverse voltage:  $V_{RRM} \leq 100 \ V$
- Low capacitance:  $C_d \le 1.5 \text{ pF}$ ■ Reverse voltage: V<sub>R</sub> ≤ 100 V Small SMD plastic package

### 1.3 Applications

High-speed switching

### 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current		<u>[1]</u> _	-	215	mA
V <sub>R</sub>	reverse voltage		-	-	100	V
t <sub>rr</sub>	reverse recovery time		[2] _	-	4	ns

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] When switched from  $I_F = 10$  mA to  $I_R = 10$  mA;  $R_L = 100 \Omega$ ; measured at  $I_R = 1$  mA.



### 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	anode		_
2	not connected		
3	cathode		1 - 2 006aaa764

## 3. Ordering information

Type number <sup>[1]</sup>	Package	Package			
	Name	Description	Version		
PMBD914	-	plastic surface-mounted package; 3 leads	SOT23		
PMBD914/DG					

### 4. Marking

Table 5. Marking codes	
Type number	Marking code <sup>[1]</sup>
PMBD914	*5D
PMBD914/DG	YB*

[1] \* = -: made in Hong Kong

- \* = p: made in Hong Kong
- \* = t: made in Malaysia
- \* = W: made in China

## 5. Limiting values

#### Table 6.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	100	V
V <sub>R</sub>	reverse voltage		-	100	V
l <sub>F</sub>	forward current		<u>[1]</u> _	215	mA
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward	square wave	[2]		
current	current	t <sub>p</sub> = 1 μs	-	4	А
		t <sub>p</sub> = 1 ms	-	1	А
		t <sub>p</sub> = 1 s	-	0.5	А

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Table 6.	Limiting	values	continued
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In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1][3]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2]  $T_j = 25 \ ^\circ C$  prior to surge.

[3] Soldering point of cathode tab.

### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R <sub>th(j-t)</sub>	thermal resistance from junction to tie-point		[2] _	-	330	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Soldering point of cathode tab.

### 7. Characteristics

#### Table 8.Characteristics

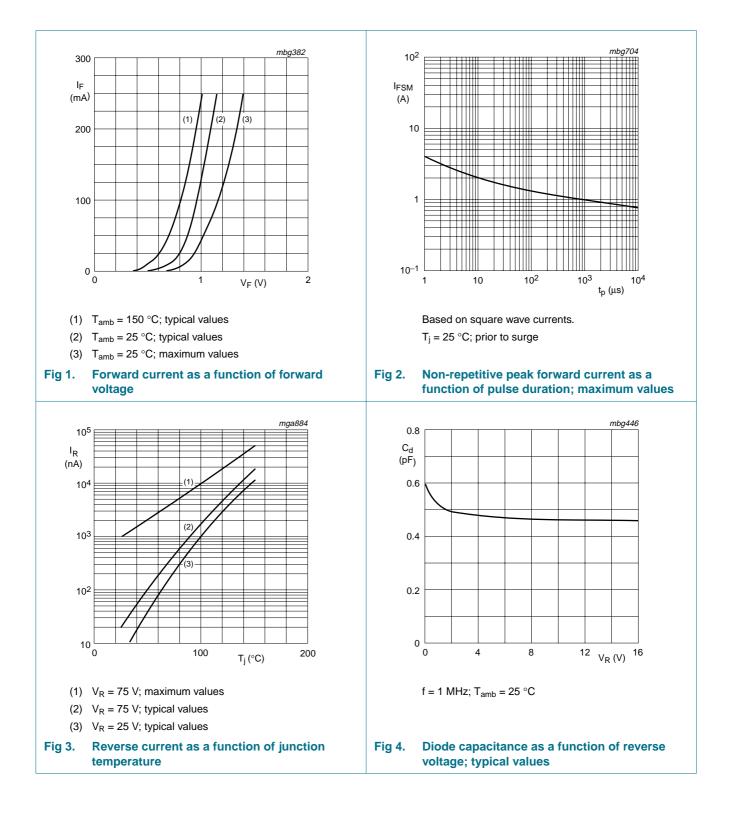
T<sub>amb</sub> = 25 °C unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F = 1 \text{ mA}$	-	-	715	mV
	I <sub>F</sub> = 10 mA	-	-	855	mV	
		I <sub>F</sub> = 50 mA	-	-	1	V
		I <sub>F</sub> = 150 mA	-	-	1.25	V
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 25 V	-	-	25	nA
		V <sub>R</sub> = 75 V	-	-	1	μΑ
		$V_R$ = 25 V; $T_j$ = 150 °C	-	-	30	μΑ
		$V_R$ = 75 V; $T_j$ = 150 °C	-	-	50	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> _	-	4	ns
$V_{FR}$	forward recovery voltage		[2] _	-	1.75	V

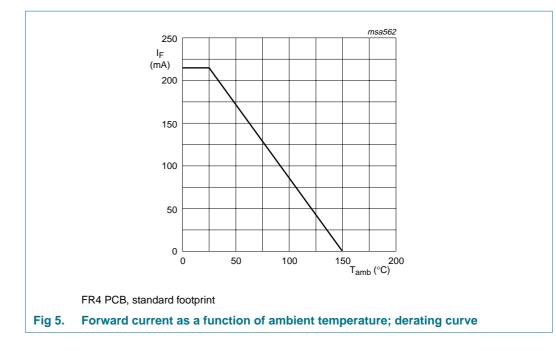
[1] When switched from I<sub>F</sub> = 10 mA to I<sub>R</sub> = 10 mA; R<sub>L</sub> = 100  $\Omega$ ; measured at I<sub>R</sub> = 1 mA.

[2] When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.

#### Single high-speed switching diode



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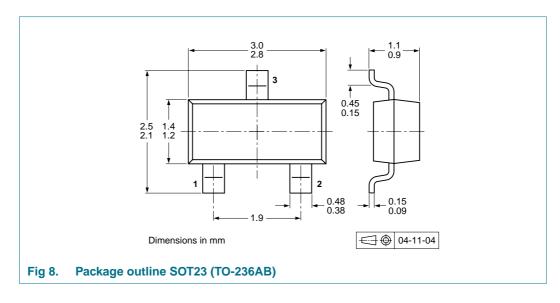


#### tr tp ₽ Æ D.U.T. Æ 10 % $R_{S} = 50 \Omega$ + I<sub>F</sub> SAMPLING OSCILLOSCOPE t $R_i = 50 \Omega$ $V = V_R + I_F \times R_S$ (1) 90 % $V_{\mathsf{R}}$ mga881 input signal output signal (1) $I_R = 1 \text{ mA}$ Reverse recovery time test circuit and waveforms Fig 6. 450 Ω 1 kΩ I V 90 % $R_S = 50 \Omega$ OSCILLOSCOPE VFR D.U.T. 💆 $R_i = 50 \Omega$ 10 % t t tr tp input signal output signal mga882 Fig 7. Forward recovery voltage test circuit and waveforms

### 8. Test information

Single high-speed switching diode

### 9. Package outline



## **10. Packing information**

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

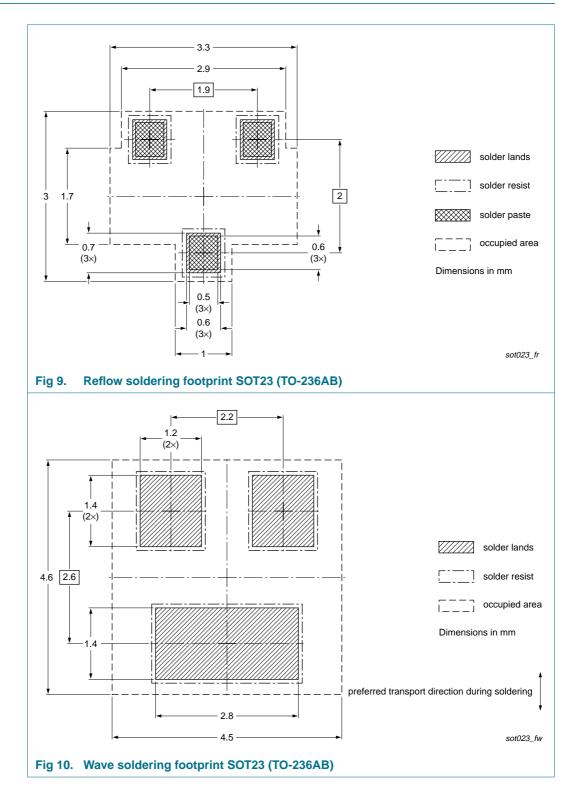
Type number <sup>[2]</sup> Package		Description	Packing	Packing quantity	
			3000	10000	
PMBD914	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
PMBD914/DG					

[1] For further information and the availability of packing methods, see Section 14.

[2] /DG: halogen-free

#### Single high-speed switching diode

### **11. Soldering**



Single high-speed switching diode

## 12. Revision history

Table 10.   Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMBD914_6	20090211	Product data sheet	-	PMBD914_5	
Modifications:	<ul> <li>Type number</li> </ul>	er PMBD914/DG added			
	<ul> <li>Section 13 "</li> </ul>	Legal information": updatec	I		
PMBD914_5	20071126	Product data sheet	-	PMBD914_4	
PMBD914_4	20040106	Product specification	-	PMBD914_3	
PMBD914_3	19990511	Product specification	-	PMBD914_2	
PMBD914_2	19960918	Product specification	-	PMBD914_1	
PMBD914_1	19960404	Product specification	-	-	

### **13. Legal information**

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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